

NPN RF POWER TRANSISTOR

DESCRIPTION

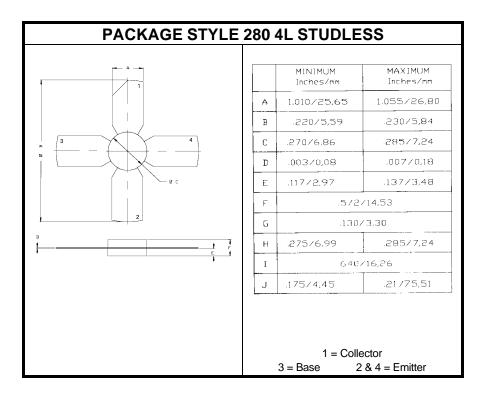
The **ASI SRF 1318** is a Common Emitter Device Designed for Class C Amplifier Applications up to 1 GHz.

FEATURES INCLUDE:

- High Gain
- Gold Metallization
- Emitter Ballasting

MAXIMUM RATINGS

Ic	1.7 A			
V _{CBO}	36 V			
P _{DISS}	15 W @ $T_C = 25$ $^{\circ}C$			
TJ	-55 °C to +200 °C			
T _{STG}	-55 °C to +200 °C			
θ _{JC}	12 ^O C/W			



CHARACTERISTICS T_c = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV _{CBO}	I _C = 10 mA	36			V
BV _{CEO}	I _C = 50 mA	16			٧
BV _{EBO}	I _E = 2.0 mA	4.0			٧
h _{FE}	$V_{CE} = 5.0 \text{ V}$ $I_{C} = 200 \text{ mA}$	20			
Сов	$V_{CB} = 12.5 \text{ V}$ f = 1.0 MHz		19		pF
*P _G					dB
*ηс					%

^{*} RF SPECIFICATIONS ARE CONTROLLED BY CUSTOMER DRAWING AND ARE PROPRIETARY.

ADVANCED SEMICONDUCTOR, INC.